

## Silicon Epitaxial Planar Type

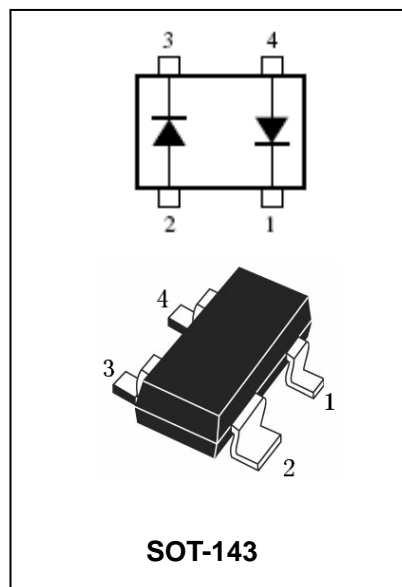
## BAT28

### FEATURES

- Two isolated elements are contained in one package, allowing high-density mounting.
- Two DIE is contained in one package (two diodes in a different direction).
- Low forward voltage  $V_F$  , optimum for low voltage Rectification.
- Optimum for high frequency rectification because of its Short reverse recovery time ( $t_{rr}$ ).



Lead-free



### APPLICATIONS

- For switching.
- For wave detection.

### ORDERING INFORMATION

Type No.	Marking	Package Code
BAT28	B43	SOT-143

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Unit
$V_R$	Rverse Voltage	30	V
$I_{FM}$	Peak Forward Current	Single	150
		Double	110
$I_F$	Forward Current	Single	30
		Double	20
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +125	$^\circ\text{C}$



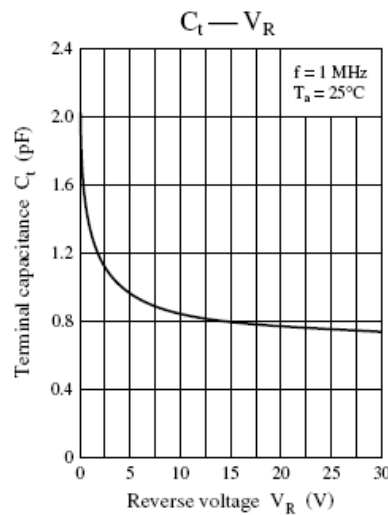
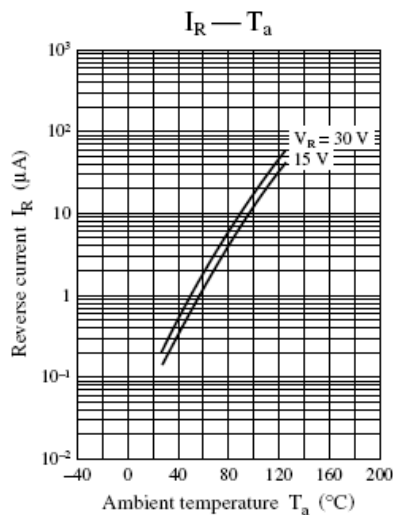
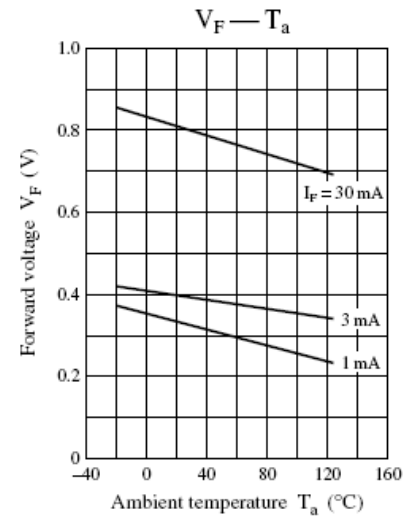
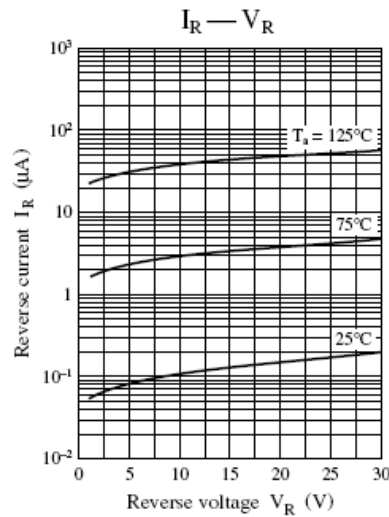
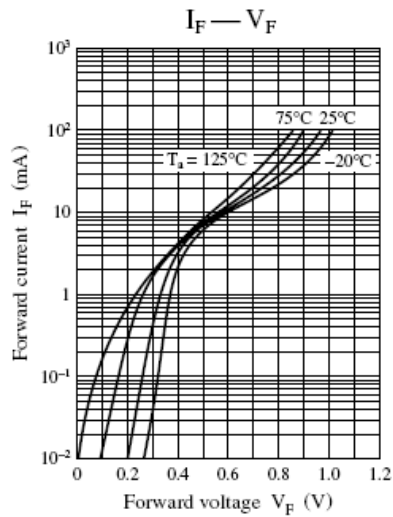
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**BAT28**

**ELECTRICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Forward Voltage	$V_F$	$I_F=1\text{mA}$	-	-	0.4	V
		$I_F=30\text{mA}$	-	-	1.3	V
Reverse Current	$I_R$	$V_R=30\text{V}$	-	-	1	$\mu\text{A}$
Total capacitance	$C_T$	$V_R=1\text{V}, f=1\text{MHz}$	-	1.5	-	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1\text{mA}, R_L=100\ \Omega$	-	1.0	-	ns
Detection efficiency	$\eta$	$V_{in}=3\text{V}, f=30\text{MHz}, R_L=3.9\text{k}\ \Omega, C_L 10\text{pF}$	-	65	-	%

**TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified**



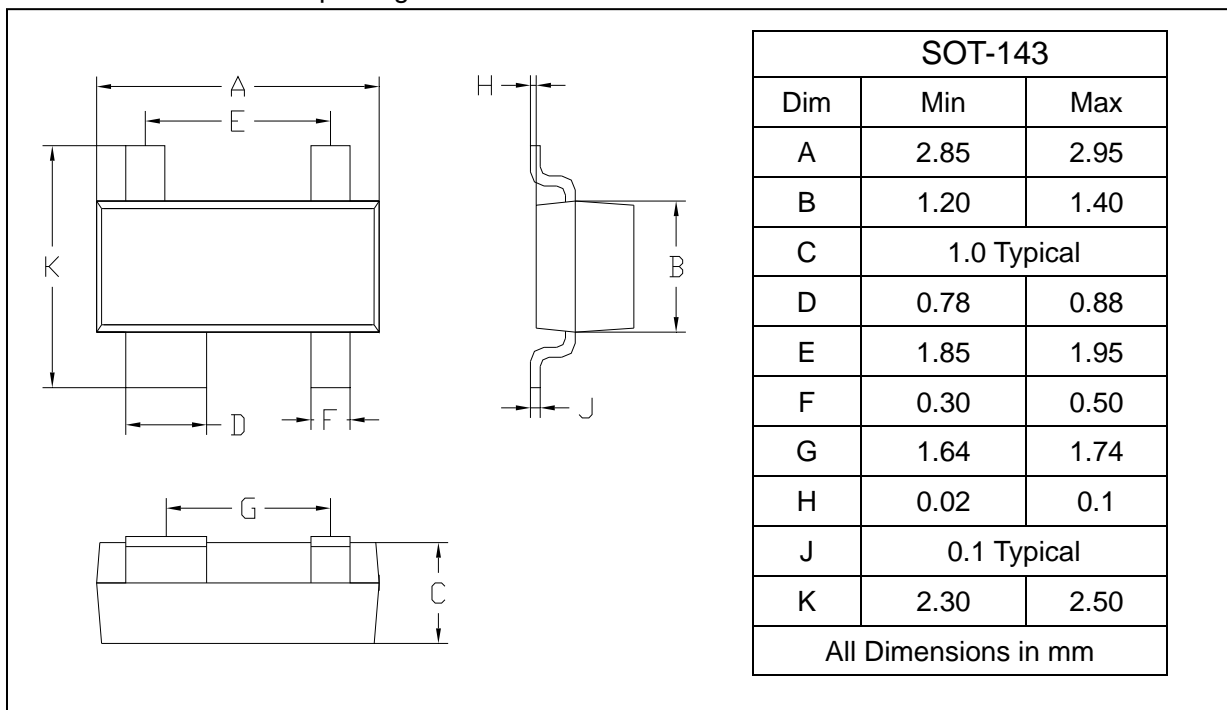
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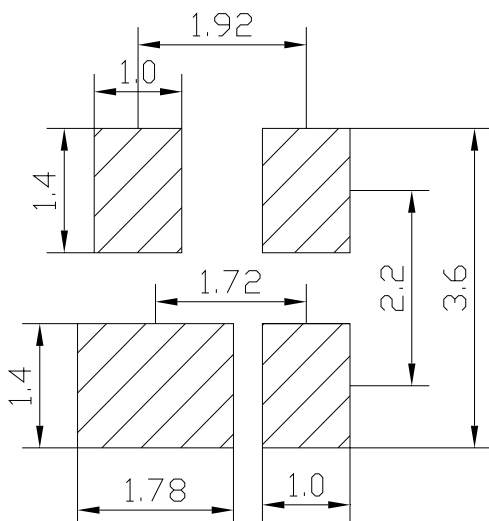
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-143



### SOLDERING FOOTPRINT



Unit : mm

### PACKAGE INFORMATION

Device	Package	Shipping
BAT28	SOT-143	3000/package